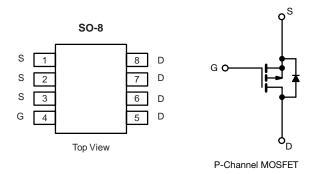


DTM9405 www.din-tek.jp

P-Channel 20 V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | |
|---------------------|-------------------------------------|---------------------------------|-----------------------|--|--|--|
| V _{DS} (V) | R _{DS(on)} (Ω) | I _D (A) ^d | Q _g (Typ.) | | | |
| - 20 | 0.012 at V_{GS} = - 4.5 V | - 12 | 36 nC | | | |
| | 0.0145 at V _{GS} = - 2.5 V | - 11 | 30 110 | | | |



FEATURES

- DT-Trench Power MOSFET
- 100 % R_g Tested
- 100 % UIS Tested

APPLICATIONS

- Adapter switch
- · Load switch
- DC/DC converters
- High speed switching
- Power management in battery-operated, mobile and wearable devices

| Pb-free |
|---------|
| BoHS |

COMPLIANT

| PARAMETER | | SYMBOL LIMIT | | UNIT | |
|--|------------------------|-----------------------------------|----------------------|------|--|
| Drain-source voltage | | V _{DS} | -20 | | |
| Gate-source voltage | | V _{GS} | ± 12 | V | |
| | T _C = 25 °C | | -12 ^e | | |
| Continuous ducin ourrent (T 150 °C) | T _C = 70 °C | | -11 | | |
| Continuous drain current ($T_J = 150 \ ^{\circ}C$) | T _A =25 °C | | -5.3 ^{b, c} | | |
| | T _A = 70 °C | Т Г | -4.5 ^{b, c} | A | |
| Pulsed drain current (t = 100 µs) | | I _{DM} | -48 ^a | | |
| | T _C = 25 °C | | -12 | | |
| Continuous source-drain diode current | T _A = 70 °C | I _S | -5.5 ^{b, c} | | |
| | T _C = 25 °C | | 3.0 | | |
| Manimum and a starting | T _C = 70 °C | | 1.92 | 14/ | |
| Maximum power dissipation | T _A = 25 °C | P _D | 1.7 ^{b, c} | W | |
| | T _A = 70 °C | 1 [| 1.1 ^{b, c} | | |
| Operating junction and storage temperature range | | T _J , T _{stg} | -55 to +150 | *0 | |
| Soldering recommendations (peak temperature) | | 1 | 260 | °C | |

THERMAL RESISTANCE RATINGS

| PARAMETER | SYMBOL | TYPICAL | MAXIMUM | UNIT | |
|----------------------------------|--------------|-------------------|---------|------|------|
| Maximum junction-to-ambient b, d | t ≤ 10 s | R _{thJA} | 40 | 50 | °C/W |
| Maximum junction-to-foot (drain) | Steady state | R _{thJF} | 15 | 20 | 0/1 |

Notes

a. Package limited

b. Surface mounted on 1" x 1" FR4 board

c. t = 10 s

d. Maximum under steady state conditions is 100 °C/W

e. $T_C = 25 \ ^{\circ}C$

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| PARAMETER SYMBOL TEST CONDITIONS | | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT | |
|---|-------------------------|--|------|--------|-------|-------|--|
| Static | | | | | | | |
| Drain-source breakdown voltage | V _{DS} | $V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$ | -20 | - | - | V | |
| V _{DS} temperature coefficient | $\Delta V_{DS}/T_{J}$ | L 050 ··· A | - | -11 | - | mV/°C | |
| V _{GS(th)} temperature coefficient | $\Delta V_{GS(th)}/T_J$ | I _D = -250 μA | - | 23.5 | - | mv/°C | |
| Gate-source threshold voltage | V _{GS(th)} | $V_{DS} = V_{GS}, I_D = -250 \ \mu A$ | -0.4 | - | -1.2 | V | |
| Gate-source leakage | I _{GSS} | V_{DS} = 0 V, V_{GS} = ± 8 V | - | - | ± 100 | nA | |
| Zaus anto coltana dusia sumant | | $V_{DS} = -16 V, V_{GS} = 0 V$ | - | - | -1 | μA | |
| Zero gate voltage drain current | I _{DSS} | $V_{DS} = -16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 55 ^{\circ}\text{C}$ | - | - | -10 | | |
| On-state drain current ^a | I _{D(on)} | $V_{DS} \le$ -5 V, V_{GS} = 0 V | -12 | - | - | А | |
| Drain-source on-state resistance ^a | R _{DS(on)} | $V_{GS} = -4.5 \text{ V}, I_D = -10 \text{ A}$ | - | 0.012 | 0.015 | Ω | |
| | US(on) | $V_{GS} = -2.5 \text{ V}, \text{ I}_{D} = -8 \text{ A}$ | - | 0.0145 | 0.020 | | |
| Forward transconductance a | g _{fs} | $V_{DS} = -10 \text{ V}, \text{ I}_{D} = -10 \text{ A}$ | - | 35 | - | S | |
| Dynamic ^b | | | - | | | | |
| Input capacitance | C _{iss} | | - | 2055 | - | | |
| Output capacitance | C _{oss} | V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz | - | 686 | - | pF | |
| Reverse transfer capacitance | C _{rss} | | - | 135 | - | | |
| Total gate charge | Qg | | - | 36 | - | | |
| Gate-source charge | Q _{gs} | V_{DS} = -10 V, V_{GS} = -4.5 V, I_{D} = -10 A | - | 6.7 | - | nC | |
| Gate-drain charge | Q _{gd} | | - | 13 | - | | |
| Gate resistance | R _g | f = 1 MHz | - | 5 | - | Ω | |
| Turn-on delay time | t _{d(on)} | | - | 61 | - | | |
| Rise time | tr | V_{DD} = -10 V, R_L = 2 Ω , $I_D \cong$ -10 A, | - | 35 | - | | |
| Turn-off delay time | t _{d(off)} | V_{GEN} = -4.5 V, R_g = 1 Ω | - | 110 | - | - ns | |
| Fall time | t _f | | - | 203 | - | | |
| Drain-Source Body Diode Characteristi | cs | | | • | | | |
| Continuous source-drain diode current | I _S | T _C = 25 °C | - | - | -12 | • | |
| Pulse diode forward current | I _{SM} | | - | - | -48 | A | |
| Body diode voltage | V _{SD} | $I_{\rm S} = -1$ A, $V_{\rm GS} = 0$ V | - | -0.6 | -1.2 | V | |
| Body diode reverse recovery time | t _{rr} | | - | 51 | - | ns | |
| Body diode reverse recovery charge | Q _{rr} | | - | 68 | - | nC | |
| Reverse recovery fall time | t _a | $I_F = -5 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{ T}_J = 25 \text{ °C}$ | - | 22 | - | | |
| Reverse recovery rise time | t _b | | - | 39 | - | ns | |

Notes

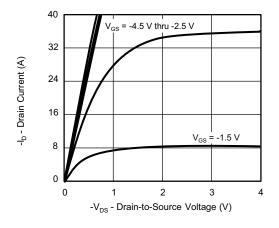
a. Pulse test; pulse width $\leq 300~\mu\text{s},~\text{duty}~\text{cycle} \leq 2~\%$

b. Guaranteed by design, not subject to production testing

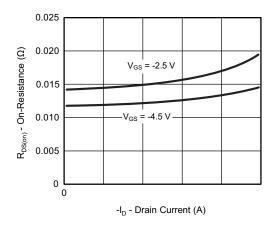
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



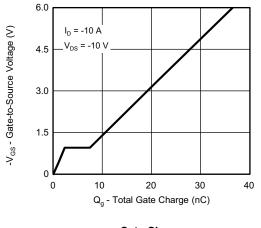
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



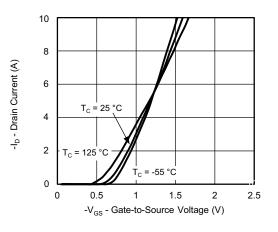
Output Characteristics



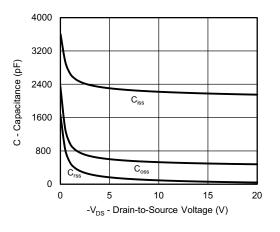
On-Resistance vs. Drain Current and Gate Voltage



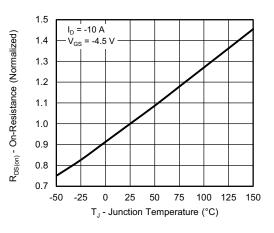
Gate Charge



Transfer Characteristics



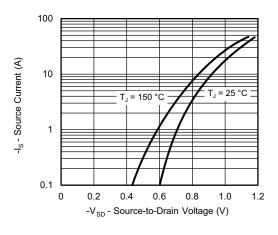




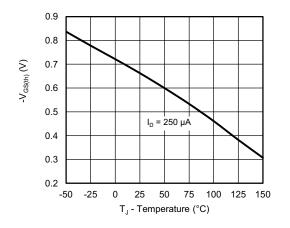
On-Resistance vs. Junction Temperature



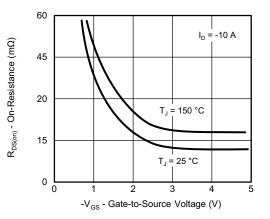
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



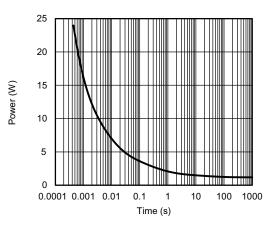
Source-Drain Diode Forward Voltage



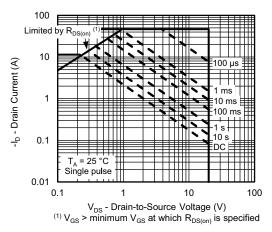
Threshold Voltage



On-Resistance vs. Gate-to-Source Voltage



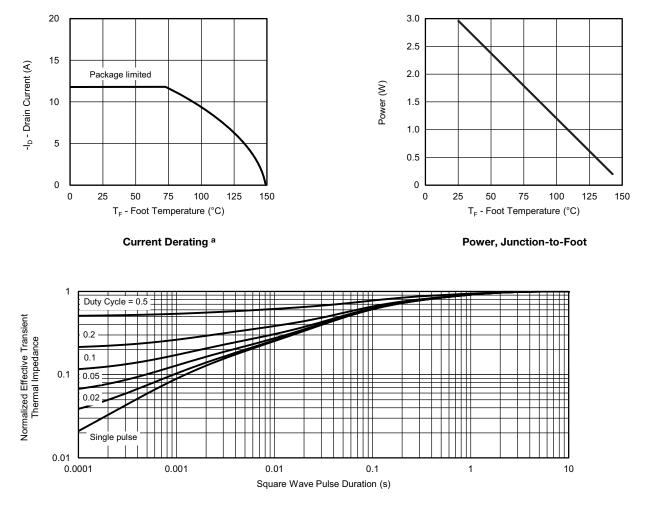
Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

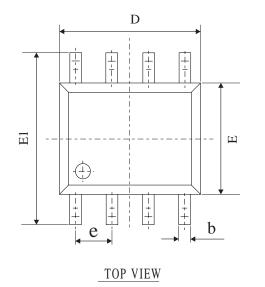


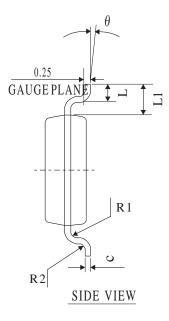
Normalized Thermal Transient Impedance, Junction-to-Foot

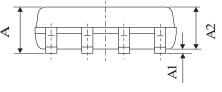
Note

a. The power dissipation P_D is based on T_J max. = 25 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

SOP-8 PACKAGE OUTLINE







SIDE VIEW

COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

| SYMBOL | MIN | ТҮР | MAX | |
|--------|---------|-------|-------|--|
| А | 1.30 | 1.60 | 1.85 | |
| Al | 0.03 | 0.15 | 0.28 | |
| A2 | 1.20 | 1.45 | 1.70 | |
| b | 0.26 | 0.40 | 0.54 | |
| С | 0.132 | 0.203 | 0.273 | |
| D | 4.50 | 4.90 | 5.30 | |
| Е | 3.50 | 3.00 | 4.30 | |
| E1 | 5.50 | 6.00 | 6.50 | |
| L | 0.30 | 0.70 | 1.10 | |
| θ | 2° | 4° | 6° | |
| L1 | 1.04REF | | | |
| e | 1.27BSC | | | |
| R1 | 0.07TYP | | | |
| R2 | 0.07TYP | | | |



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